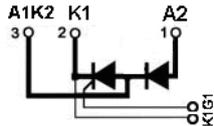


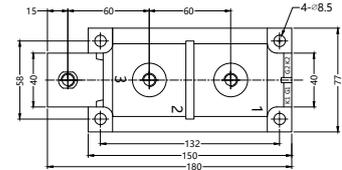
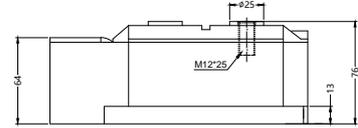
# STD800GK18PT

## Thyristor-Diode Modules



Type	V <sub>RSM</sub> V <sub>DSM</sub> V	V <sub>RRM</sub> V <sub>DRM</sub> V
STD800GK12PT	1300	1200
STD800GK14PT	1500	1400
STD800GK16PT	1700	1600
STD800GK18PT	1900	1800
STD800GK20PT	2100	2000
STD800GK22PT	2300	2200
STD800GK24PT	2500	2400
STD800GK26PT	2700	2600
STD800GK28PT	2900	2800
STD800GK30PT	3100	3000

### Dimensions in mm



Symbol	Test Conditions	Maximum Ratings	Unit
I <sub>TAV</sub>	T <sub>C</sub> =85°C; 180° half sine wave, 50Hz	800	A
I <sub>TRMS</sub>	T <sub>C</sub> =85°C; 180° Full cycle sine wave, 50Hz	1256	A
I <sub>TSM</sub> I <sub>t</sub> <sup>2</sup>	T <sub>VJ</sub> =T <sub>VJM</sub> T <sub>C</sub> =25°C 180° half sine wave, 50Hz, single pulse; V <sub>R</sub> = 0 ; Gate pulse: 20V , 5W, 1us rise time, 500us	30.0 35.0	kA
	T <sub>VJ</sub> =T <sub>VJM</sub> T <sub>C</sub> =25°C non repetitive, I <sub>T</sub> =I <sub>TAVM</sub>	4500 6125	A <sup>2</sup> s·10 <sup>3</sup>
V <sub>DRM</sub> , V <sub>RRM</sub>	T <sub>VJ</sub> =T <sub>VJM</sub> 180° half sine wave, 50Hz ; Gate open	1000/1800	V
V <sub>DSM</sub> , V <sub>RSM</sub>	T <sub>VJ</sub> =T <sub>VJM</sub> 180° half sine wave, 50Hz ; single pulse, Gate open	1100/1900	
(di/dt) <sub>cr</sub>	T <sub>VJ</sub> =T <sub>VJM</sub> f=50Hz, t <sub>p</sub> =200us V <sub>D</sub> =2/3V <sub>DRM</sub> I <sub>G</sub> =1A di <sub>G</sub> /dt=1A/us repetitive, I <sub>T</sub> =960A	100	A/us
	non repetitive, I <sub>T</sub> =I <sub>TAVM</sub>	200	
(dv/dt) <sub>cr</sub>	T <sub>VJ</sub> =T <sub>VJM</sub> ; R <sub>GK</sub> =∞; method 1 (linear voltage rise) V <sub>DR</sub> =2/3V <sub>DRM</sub>	1000	V/us
P <sub>GM</sub>	T <sub>VJ</sub> =T <sub>VJM</sub>	40	W
P <sub>GAV</sub>	T <sub>VJ</sub> =T <sub>VJM</sub>	6	W
V <sub>RGM</sub>	T <sub>VJ</sub> =T <sub>VJM</sub>	5	V
T <sub>VJ</sub> T <sub>VJM</sub> T <sub>stg</sub>		-40...+140 140 -40...+125	°C
V <sub>ISOL</sub>	50/60Hz, RMS I <sub>ISOL</sub> ≤1mA t=1min t=1s	3000 3600	V~
M <sub>d</sub>	Mounting torque (M6) Terminal connection torque (M8)	4.5-7/40-60 11-13/97-115	Nm/lb.in.
Weight	Typical	3356	g

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## Thyristor-Diode Modules

Symbol	Test Conditions	Characteristic Values	Unit
<b>IRRM</b>	$T_{VJ}=T_{VJM}; V_R=V_{RRM}$	70	mA
<b>V<sub>T</sub></b>	$I_T=1200A; T_{VJ}=25^{\circ}C$	1.55	V
<b>V<sub>TO</sub></b>	For power-loss calculations only ( $T_{VJ}=T_{VJM}$ )	0.9	V
<b>r<sub>T</sub></b>		0.21	mΩ
<b>V<sub>GT</sub></b>	$V_D=12V; T_{VJ}=25^{\circ}C$ $T_{VJ}=-40^{\circ}C$	2.5 3.5	V
<b>I<sub>GT</sub></b>	$V_D=12V; T_{VJ}=25^{\circ}C$ $T_{VJ}=-40^{\circ}C$	300 400	mA
<b>V<sub>GD</sub></b>	$T_{VJ}=T_{VJM}; V_D=2/3V_{DRM}$	0.5	V
<b>I<sub>GD</sub></b>	$T_{VJ}=T_{VJM}; V_D=2/3V_{DRM}$	10	mA
<b>I<sub>L</sub></b>	$T_{VJ}=25^{\circ}C; t_p=30\mu s; V_D=12V$ $I_G=1A; di_G/dt=1A/\mu s$	1000	mA
<b>I<sub>H</sub></b>	$T_{VJ}=25^{\circ}C; V_D=12V; R_{GK}=\infty$	500	mA
<b>t<sub>gd</sub></b>	$T_{VJ}=25^{\circ}C; V_D=1/2V_{DRM}$ $I_G=1A; di_G/dt=1A/\mu s$	10	us
<b>t<sub>q</sub></b>	$T_{VJ}=T_{VJM}; I_T=500A; t_p=200\mu s; -di/dt=10A/\mu s$ $V_R=100V; dv/dt=50V/\mu s; V_D=2/3V_{DRM}$	200	us
<b>R<sub>thJC</sub></b>	DC current per module	0.0405	K/W
<b>R<sub>thJK</sub></b>	DC current per module	0.01	K/W
<b>ds</b>	Creeping distance on surface	12.7	mm
<b>dA</b>	Creepage distance in air	9.6	mm
<b>a</b>	Maximum allowable acceleration	59.81	m/s <sup>2</sup>

### FEATURES

- \* International standard package
- \* Pressure Contacts for high reliability
- \* Isolation voltage 3600 V~
- \* UL File NO.E310749
- \* RoHS compliant

### APPLICATIONS

- \* Motor control, softstarter
- \* Power converter
- \* Heat and temperature control for industrial furnaces and chemical processes
- \* Lighting control
- \* Solid state switches

### ADVANTAGES

- \* Simple mounting
- \* Improved temperature and power cycling
- \* Reduced protection circuits



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# STD800GK18PT

## Thyristor-Diode Modules

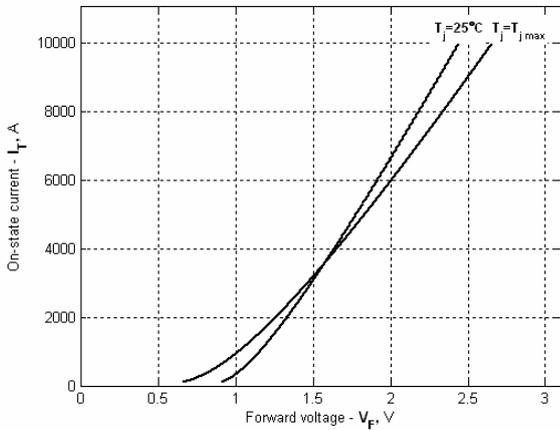


Fig 1 On-state characteristics

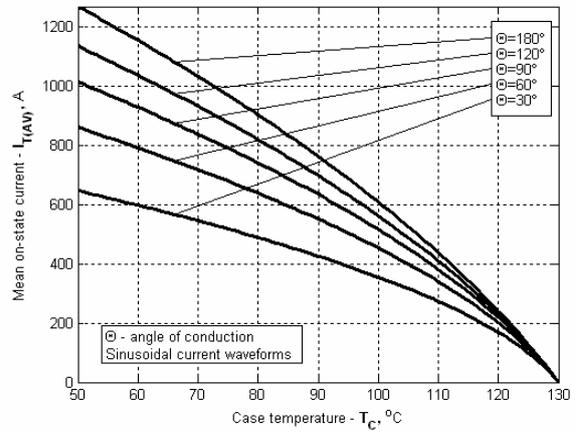


Fig 2 Mean on-state current  $I_{TAV}$  vs. Case temperature  $T_C$  for sinusoidal current waveforms at different conduction angles,  $f=50\text{Hz}$

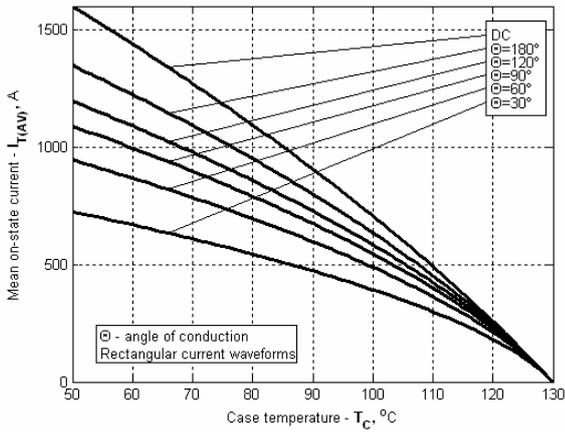


Fig 3 Mean on-state current  $I_{TAV}$  vs. Case temperature  $T_C$  for rectangular current waveforms at different conduction angles and for DC,  $f=50\text{Hz}$

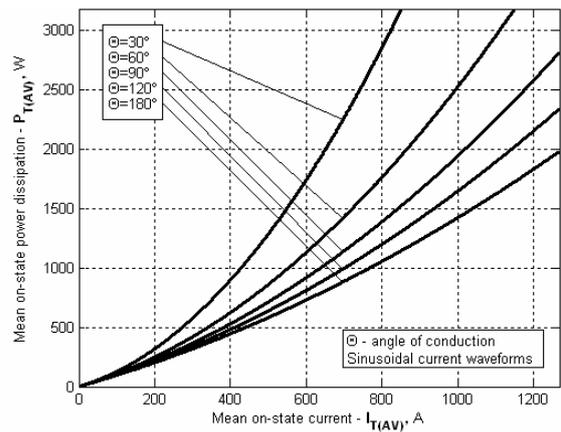


Fig 4 Mean on-state power dissipation  $P_{TAV}$  vs. Mean on-state current  $I_{TAV}$  for sinusoidal current waveforms at different conduction angles,  $f=50\text{Hz}$

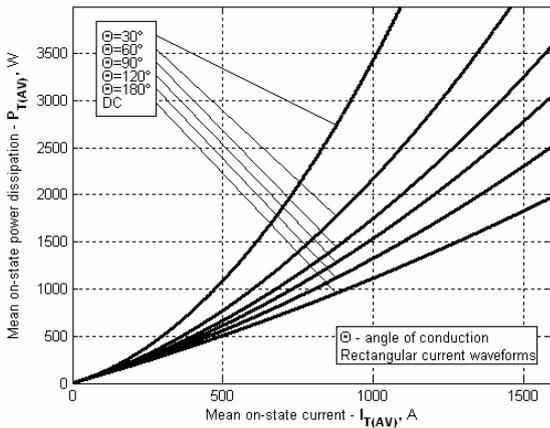


Fig 5 Mean on-state power dissipation  $P_{TAV}$  vs. Mean on-state current  $I_{TAV}$  for rectangular current waveforms at different conduction angles and for DC,  $f=50\text{Hz}$

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## Thyristor-Diode Modules

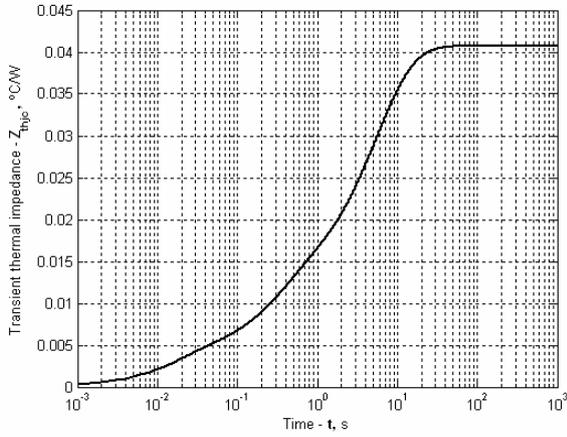


Fig 6 Transient thermal impedance junction to case  $Z_{thjc}$  per arm for DC

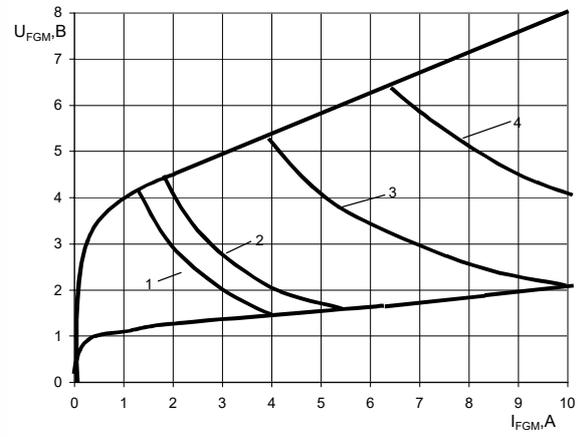


Fig 7 Gate characteristic